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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DDR, PCIe, SERDES
Connectivity	CANbus, Ethernet, I ² C, SPI, UART/USART, USB
Speed	166MHz
Primary Attributes	FPGA - 10K Logic Modules
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	400-LFBGA
Supplier Device Package	400-VFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m2s010t-vf400

Table 15 Inrush Currents at Power up, $40\text{ }^{\circ}\text{C} \leq T_J \leq 100\text{ }^{\circ}\text{C}$ Typical Process

Power Supplies	Voltage (V)	005	010	025	050	060	090	150	Unit
V_{DD}	1.26	25	32	38	48	45	77	109	mA
V_{PP}	3.46	33	49	36	180	13	36	51	mA
V_{DDI}	2.62	134	141	161	187	93	272	388	mA
Number of banks		7	8	8	10	10	9	19	

2.3.3 Average Fabric Temperature and Voltage Derating Factors

The following table lists the average temperature and voltage derating factors for fabric timing delays normalized to $T_J = 85\text{ }^{\circ}\text{C}$, in worst-case $V_{DD} = 1.14\text{ V}$.

Table 16 Average Junction Temperature and Voltage Derating Factors for Fabric Timing Delays

Array Voltage V_{DD} (V)	40 °C	0 °C	25 °C	70 °C	85 °C	100 °C
1.14	0.83	0.89	0.92	0.98	1.00	1.02
1.2	0.75	0.80	0.83	0.89	0.91	0.93
1.26	0.69	0.73	0.76	0.81	0.83	0.85

2.3.5.5 Detailed I/O Characteristics

Table 24 Input Capacitance, Leakage Current, and Ramp Time

Symbol	Description	Maximum	Unit	Conditions
C_{IN}	Input capacitance	10	pF	
I_{IL} (dc)	Input current low (Applicable to HSTL/SSTL inputs only)	400	μA	$V_{DDI} = 2.5 \text{ V}$
		500	μA	$V_{DDI} = 1.8 \text{ V}$
		600	μA	$V_{DDI} = 1.5 \text{ V}^{\dagger}$
	Input current low (Applicable to all other digital inputs)	10	μA	
I_{IH} (dc)	Input current high (Applicable to HSTL/SSTL inputs only)	400	μA	$V_{DDI} = 2.5 \text{ V}$
		500	μA	$V_{DDI} = 1.8 \text{ V}$
		600	μA	$V_{DDI} = 1.5 \text{ V}^{\dagger}$
	Input current high (Applicable to all other digital inputs)	10	μA	
T_{RAMPIN}^2	Input ramp time (Applicable to all digital inputs)	50	ns	

1. Applicable when I/O pair is programmed with an HSTL/SSTL I/O type on IOP and an un-terminated I/O type (LVCMOS, for example) on ION pad.
2. Voltage ramp must be monotonic.

The following table lists the minimum and maximum I/O weak pull-up/pull-down resistance values of DDRIO I/O bank at V_{OH}/V_{OL} Level.

Table 25 I/O Weak Pull-up/Pull-down Resistances for DDRIO I/O Bank

V_{DDI} Domain	R(WEAK PULL-UP) at V_{OH} (:)		R(WEAK PULL-DOWN) at V_{OL} (:)	
	Min	Max	Min	Max
2.5 V ^{1, 2}	10K	17.8K	9.98K	18K
1.8 V ^{1, 2}	10.3K	19.1K	10.3K	19.5K
1.5 V ^{1, 2}	10.6K	20.2K	10.6K	21.1K
1.2 V ^{1, 2}	11.1K	22.7K	11.2K	24.6K

1. $R(\text{WEAK PULL-DOWN}) = (V_{OL\text{spec}})/I(\text{WEAK PULL-DOWN MAX})$.
2. $R(\text{WEAK PULL-UP}) = (V_{DDI\text{max}} - V_{OH\text{spec}})/I(\text{WEAK PULL-UP MIN})$.

Table 46 LVCMOS 2.5 V Transmitter Characteristics for DDRIO Bank (Output and Tristate Buffers) (continued)

Output Drive Selection	Slew Control	T _{DP}		T _{ZL}		T _{ZH}		T _{HZ} ¹		T _{LZ} ¹		Unit
		1	Std	1	Std	1	Std	1	Std	1	Std	
4 mA	Slow	3.095	3.641	2.705	3.182	3.088	3.633	4.738	5.575	4.348	5.116	ns
	Medium	2.825	3.324	2.488	2.927	2.823	3.321	4.492	5.285	4.063	4.781	ns
	Medium fast	2.701	3.178	2.384	2.804	2.698	3.173	4.364	5.135	3.945	4.642	ns
	Fast	2.69	3.165	2.377	2.796	2.687	3.161	4.359	5.129	3.94	4.636	ns
6 mA	Slow	2.919	3.434	2.491	2.93	2.902	3.414	5.085	5.983	4.674	5.5	ns
	Medium	2.65	3.118	2.279	2.681	2.642	3.108	4.845	5.701	4.375	5.148	ns
	Medium fast	2.529	2.975	2.176	2.56	2.522	2.965	4.724	5.558	4.259	5.011	ns
	Fast	2.516	2.96	2.168	2.551	2.508	2.95	4.717	5.55	4.251	5.002	ns
8 mA	Slow	2.863	3.368	2.427	2.855	2.844	3.346	5.196	6.114	4.769	5.612	ns
	Medium	2.599	3.058	2.217	2.608	2.59	3.047	4.952	5.827	4.471	5.261	ns
	Medium fast	2.483	2.921	2.114	2.482	2.473	2.91	4.832	5.685	4.364	5.134	ns
	Fast	2.467	2.902	2.106	2.478	2.457	2.89	4.826	5.678	4.348	5.116	ns
12 mA	Slow	2.747	3.232	2.296	2.701	2.724	3.204	5.39	6.342	4.938	5.81	ns
	Medium	2.493	2.934	2.20	2.473	2.483	2.921	5.166	6.078	4.65	5.471	ns
	Medium fast	2.382	2.803	2.006	2.36	2.372	2.789	5.067	5.962	4.546	5.349	ns
	Fast	2.369	2.787	1.999	2.352	2.357	2.72	5.063	5.958	4.538	5.339	ns
16 mA	Slow	2.677	3.149	2.213	2.604	2.649	3.116	5.575	6.56	5.08	5.977	ns
	Medium	2.432	2.862	2.02	2.386	2.421	2.848	5.372	6.32	4.801	5.649	ns
	Medium fast	2.324	2.734	1.937	2.272	2.311	2.718	5.297	6.233	4.7	5.531	ns
	Fast	2.313	2.721	1.929	2.269	2.3	2.706	5.296	6.231	4.699	5.529	ns

1. Delay increases with drive strength are inherent to built-in control circuitry for simultaneous switching output (SSO) management.

Table 47 LVCMOS 2.5 V Transmitter Characteristics for MSIO Bank (Output and Tristate Buffers)

Output Drive Selection	Slew Control	T _{DP}		T _{ZL}		T _{ZH}		T _{HZ} ¹		T _{LZ} ¹		Unit
		1	Std	1	Std	1	Std	1	Std	1	Std	
2 mA	Slow	3.48	4.095	3.855	4.534	3.785	4.453	2.12	2.494	3.45	4.059	ns
4 mA	Slow	2.583	3.039	3.042	3.579	3.138	3.691	4.143	4.874	4.687	5.513	ns
6 mA	Slow	2.392	2.815	2.669	3.139	2.822	3.317	4.909	5.775	5.083	5.98	ns
8 mA	Slow	2.309	2.717	2.565	3.017	2.74	3.223	5.812	6.837	5.523	6.497	ns
12 mA	Slow	2.333	2.745	2.437	2.867	2.76	3.089	6.131	7.213	5.712	6.72	ns
16 mA	Slow	2.412	2.838	2.335	2.747	2.538	2.979	6.54	7.694	6.007	7.067	ns

1. Delay increases with drive strength are inherent to built-in control circuitry for simultaneous switching output (SSO) management.

Table 85 LVCMOS 1.2 V Transmitter Characteristics for MSIOD I/O Bank (Output and Tristate Buffers)

Output Drive Selection	Slew Control	T _{DP}		T _{ZL}		T _{ZH}		T _{HZ} ¹		T _{LZ} ¹		Unit
		1	Std	1	Std	1	Std	1	Std	1	Std	
2 mA	Slow	3.883	4.568	4.868	5.726	5.329	6.269	7.994	9.404	7.527	8.855	ns
4 mA	Slow	3.774	4.44	4.188	4.926	4.613	5.426	8.972	10.555	8.315	9.782	ns

1. Delay increases with drive strength are inherent to buffer control circuitry for simultaneous switching output (SSO) management.

2.3.5.11 3.3 V PCI/PCIX

Peripheral Component Interface (PCI) for 3.3 V devices specify support for 33 MHz and 66 MHz PCI bus applications.

Minimum and Maximum DC/AC Input and Output Levels Specification (Applicable to MSIO Bank Only)

Table 86 PCI/PCI-X DC Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{DDI}	3.15	3.3	3.45	V

Table 87 PCI/PCI-X DC Input Voltage Specification

Parameter	Symbol	Min	Max	Unit
DC input voltage	V	0	3.45	V
Input current high	I _{IH} (DC)			
Input current low	I _{IL} (DC)			

1. See Table 24, page 22

Table 88 PCI/PCI-X DC Output Voltage Specification

Parameter	Symbol	Min	Typ	Max	Unit
DC output logic high	V _H		Per PCI specification		V
DC output logic low	V _L		Per PCI specification		V

Table 89 PCI/PCI-X Minimum and Maximum AC Switching Speed

Parameter	Symbol	Max	Unit	Conditions
Maximum data rate (MSIO I/O bank)	M _{DR}	630	Mbps	AC Loading: per JEDEC specifications

Table 90 PCI/PCI-X AC Test Parameter Specifications

Parameter	Symbol	Typ	Unit
Measuring/trip point for data path (falling edge)	T _{TRIP} V	0.615 × V _{DDI}	V
Measuring/trip point for data path (rising edge)	T _{TRIP} V	0.285 × V _{DDI}	V
Resistance for data test path	R _{TT_TEST}	25	Ω
Resistance for enable path (T _{ZH} , T _{ZL} , T _{HZ} , T _{LZ})	R _{ENT}	2K	Ω
Capacitive loading for enable path (T _{ZH} , T _{ZL} , T _{HZ} , T _{LZ})	C _{ENT}	5	pF
Capacitive loading for data path (T _{ZH} , T _{ZL} , T _{HZ} , T _{LZ})	C _{LOAD}	10	pF

AC Switching Characteristics

Worst commercial-case conditions: $T = 85\text{ }^{\circ}\text{C}$, $V_D = 1.14\text{ V}$, $V_{DI} = 3.0\text{ V}$

Table 91 PCI/PCIX AC Switching Characteristics for Receiver for MSIO I/O Bank (Input Buffers)

On-Die Termination (ODT)	T_{PY}		T_{PYS}		Unit
	1	Std	1	Std	
None	2.229	2.623	2.238	2.633	ns

Table 92 PCI/PCIX AC switching Characteristics for Transmitter for MSIO I/O Bank (Output and Tristate Buffers)

T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
1	Std	1	Std	1	Std	1	Std	1	Std	
2.146	2.525	2.043	2.404	2.084	4.52	6.095	7.171	5.558	6.539	ns

2.3.6 Memory Interface and Voltage Referenced I/O Standards

This section describes High-Speed Transceiver Logic (HSTL) memory interface and voltage reference I/O standards.

2.3.6.1 High-Speed Transceiver Logic (HSTL)

The HSTL standard is a general purpose high-speed bus standard sponsored by IBM (EIA/JESD8-6). IGLOO2 FPGA and SmartFusion2 SoC FPGA devices support two classes of the 1.5 V HSTL. These differential versions of the standard require a differential amplifier input buffer and a push-pull output buffer.

Minimum and Maximum DC/AC Input and Output Levels Specification (Applicable to DDRIO Bank Only)

Table 93 HSTL Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{DI}	1.425	1.5	1.575	V
Termination voltage	V_T	0.698	0.750	0.803	V
Input reference voltage	V_{REF}	0.698	0.750	0.803	V

Table 94 HSTL DC Input Voltage Specification

Parameter	Symbol	Min	Max	Unit
DC input logic high	V_H (DC)	$V_{REF} + 0.1$	1.575	V
DC input logic low	V_L (DC)	0.3	$V_{REF} - 0.1$	V
Input current high	I_{IH} (DC)			
Input current low	I_{IL} (DC)			

1. See Table 24, page 22

Table 112 SSTL2 Receiver Characteristics for MSIO I/O Bank(Input Buffers)

	On-Die Termination (ODT)	T_{PY}		
		1	Std	Unit
Pseudo differential	None	2.798	3.293	ns
True differential	None	2.733	3.215	ns

Table 113 DDR1/SSTL2 Receiver Characteristics for MSIOD I/O Bank (Input Buffers)

	On-Die Termination (ODT)	T_{PY}		
		1	Std	Unit
Pseudo differential	None	2.476	2.913	ns
True differential	None	2.475	2.911	ns

Table 114 SSTL2 Class I Transmitter Characteristics for DDRIO I/O Bank(Output and Tristate Buffers)

	T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
Single-ended	2.26	2.66	1.99	2.341	1.985	2.335	2.135	2.512	2.13	2.505	ns
Differential	2.26	2.658	2.202	2.592	2.02	2.589	2.393	2.815	2.392	2.814	ns

Table 115 DDR1/SSTL2 Class I Transmitter Characteristics for MSIO I/O Bank(Output and Tristate Buffers)

	T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
Single-ended	2.055	2.417	2.037	2.392	2.03	2.388	2.068	2.433	2.061	2.425	ns
Differential	2.192	2.58	2.434	2.864	2.2	2.852	2.164	2.545	2.156	2.536	ns

Table 116 DDR1/SSTL2 Class I Transmitter Characteristics for MSIOD I/O Bank (Output and Tristate Buffers)

	T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
Single-ended	1.512	1.779	1.462	1.72	1.462	1.72	1.676	1.972	1.676	1.971	ns
Differential	1.676	1.971	1.774	2.087	1.66	2.077	1.854	2.181	1.845	2.171	ns

Table 117 DDR1/SSTL2 Class II Transmitter Characteristics for DDRIO I/O Bank (Output and Tristate Buffers)

	T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
Single-ended	2.122	2.497	1.906	2.243	1.902	2.237	2.061	2.424	2.056	2.418	ns
Differential	2.127	2.501	2.042	2.402	2.042	2.403	2.363	2.78	2.365	2.781	ns

Table 128 DDR2/SSTL18 Transmitter Characteristics (Output and Tristate Buffers)

	T _{DP}		T _{ZL}		T _{ZH}		T _{HZ}		T _{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
SSTL18 Class I (for DDRIO I/O Bank)											
Single-ended	2.383	2.804	2.23	2.623	2.29	2.622	2.202	2.591	2.201	2.59	ns
Differential	2.413	2.84	2.797	3.29	2.797	3.29	2.282	2.685	2.282	2.685	ns
SSTL18 Class II (for DDRIO I/O Bank)											
Single-ended	2.281	2.683	2.196	2.584	1.95	2.583	2.171	2.555	2.17	2.554	ns
Differential	2.315	2.724	2.698	3.173	2.698	3.173	2.242	2.639	2.242	2.639	ns

2.3.6.5 Stub-Series Terminated Logic 1.5 V (SSTL15)

SSTL15 Class I and Class II are supported in IGLOO2 FPGAs and SmartFusion2 SoC FPGAs, and also comply with the reduced and full drive double data rate (DDR3) standard. IGLOO2 FPGA and SmartFusion2 SoC FPGA I/Os supports both standards for single-ended signaling and differential signaling for SSTL18. This standard requires a differential amplifier input buffer and a push-pull output buffer.

Minimum and Maximum DC/AC Input and Output Levels Specification

The following table lists the SSTL15 DC voltage specifications for DDRIO bank.

Table 129 SSTL15 DC Recommended DC Operating Conditions (for DDRIO I/O Bank Only)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{DI}	1.425	1.5	1.575	V
Termination voltage	V _T	0.698	0.750	0.803	V
Input reference voltage	V _{REF}	0.698	0.750	0.803	V

Table 130 SSTL15 DC Input Voltage Specification (for DDRIO I/O Bank Only)

Parameter	Symbol	Min	Max	Unit
DC input logic high	V _{IH} (DC)	V _{REF} + 0.1	1.575	V
DC input logic low	V _{IL} (DC)	0.3	V _{REF} - 0.1	V
Input current high	I _{IH} (DC)			
Input current low	I _{IL} (DC)			

1. See Table 24, page 22

Table 150 LPDDR Full Drive for DDRIO I/O Bank (Output and Tristate Buffers)

	T_{DP}		T_{ENZL}		T_{ENZH}		T_{ENHZ}		T_{ENLZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
Single-ended	2.281	2.683	2.196	2.584	2.196	2.583	2.171	2.55	2.17	2.554	ns
Differential	2.298	2.703	2.288	2.692	2.288	2.692	2.593	3.051	2.593	3.051	ns

Minimum and Maximum DC/AC Input and Output Levels Specification using LPDDR-LVCMOS 1.8 V Mode

Table 151 LPDDR-LVCMOS 1.8 V Mode Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{DDI}	1.710	1.8	1.89	V

Table 152 LPDDR-LVCMOS 1.8 V Mode DC Input Voltage Specification

Parameter	Symbol	Min	Max	Unit
DC input logic high (for MSIOD and DDRIO I/O banks)	$V_{IH} (DC)$	$0.65 \times V_{DDI}$	1.89	V
DC input logic high (for MSIO I/O bank)	$I_{IH} (DC)$	$0.65 \times V_{DDI}$	3.45	V
DC input logic low	$V_{IL} (DC)$	0.3	$0.35 \times V_{DDI}$	V
Input current high	$I_{IH} (DC)$			
Input current low	$I_{IL} (DC)$			

1. See Table 24, page 22

Table 153 LPDDR-LVCMOS 1.8 V Mode DC Output Voltage Specification

Parameter	Symbol	Min	Max	Unit
DC output logic high	V_{OH}	V_{DDI}	0.45	V
DC output logic low	V_{OL}		0.45	V

Table 154 LPDDR-LVCMOS 1.8 V Minimum and Maximum AC Switching Speeds

Parameter	Symbol	Max	Unit	Conditions
Maximum data rate (f DDRIO I/O bank)	f_{MAX}	400	Mbps	AC loading: 17pf load, 8 ma drive and above/all slew

Table 155 LPDDR-LVCMOS 1.8 V Calibrated Impedance Option

Parameter	Symbol	Typ	Unit
Supported output driver calibrated impedance (for DDRIO I/O bank)	RODT_CAL	75, 60, 50, 33, 25, 20	:

Table 159 LPDDR-LVCMOS 1.8 V AC Switching Characteristics for Transmitter for DDRIO I/O Bank (Output and Tristate Buffers) (continued)

	medium	3.246	3.819	2.686	3.16	3.233	3.807	5.542	6.52	4.936	5.807	ns
	medium_fast	3.066	3.607	2.525	2.970	3.054	3.593	5.405	6.359	4.811	5.66	ns
	fast	3.046	3.584	2.513	2.957	3.0	3.57	5.401	6.353	4.803	5.651	ns
10 mA	slow	3.498	4.115	2.878	3.384	3.483	4.096	6.046	7.113	5.444	6.404	ns
	medium	3.138	3.692	2.569	3.023	3.1	3.678	5.782	6.803	5.129	6.034	ns
	medium_fast	2.966	3.489	2.414	2.822	2.951	3.472	5.666	6.665	5.013	5.897	ns
	fast	2.945	3.464	2.401	2.826	2.9	3.448	5.659	6.658	5.003	5.886	ns
12 mA	slow	3.417	4.02	2.807	3.303	3.403	4.002	6.083	7.156	5.464	6.428	ns
	medium	3.076	3.618	2.519	2.964	3.0	3.604	5.828	6.856	5.176	6.089	ns
	medium_fast	2.913	3.427	2.376	2.792	2.898	3.41	5.725	6.736	5.072	5.966	ns
	fast	2.894	3.405	2.362	2.78	2.873	3.388	5.715	6.724	5.064	5.957	ns
16 mA	slow	3.366	3.96	2.751	3.237	3.343	3.939	6.226	7.324	5.576	6.56	ns
	medium	3.03	3.565	2.47	2.906	3.017	3.55	5.981	7.036	5.282	6.214	ns
	medium_fast	2.87	3.377	2.328	2.739	2.852	3.358	5.895	6.935	5.18	6.094	ns
	fast	2.853	3.357	2.314	2.723	2.8	3.338	5.889	6.929	5.177	6.09	ns

1. Delay increases with drive strength are inherent to bus driver control circuitry for simultaneous switching output (SSO) management).

2.3.7 Differential I/O Standards

Configuration of the I/O modules as a differential pair is handled by Microsemi SoC Products Group Libero software when the user instantiates a differential I/O macro in the design. Differential I/Os can also be used in conjunction with the buffered input register (InReg), Output register (OutReg), Enable register (EnReg), and Double Data Rate registers (DDR).

2.3.7.1 LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard.

Minimum and Maximum Input and Output Levels

Table 160 LVDS Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Supply voltage	V_{DI}	2.375	2.5	2.625	V	2.5 V range
Supply voltage	V_{DI}	3.15	3.3	3.45	V	3.3 V range

Table 161 LVDS DC Input Voltage Specification

Parameter	Symbol	Min	Max	Unit	Conditions
DC Input voltage	V	0	2.925	V	2.5 V range
DC input voltage	V	0	3.45	V	3.3 V range
Input current high	I_{IH} (DC)				
Input current low	I_{IL} (DC)				

1. See Table 24, page 22

Table 168 LVDS25 Receiver Characteristics for MSIOD I/O Bank (Input Buffers)

On-Die Termination (ODT)	T _{py}		
	1	Std	Unit
None	2.554	3.004	ns
100	2.549	2.999	ns

Table 169 LVDS25 Transmitter Characteristics for MSIO I/O Bank (Output and Tristate Buffers)

T _{DP}		T _{ZL}		T _{ZH}		T _{HZ}		T _{LZ}		Unit
1	Std	1	Std	1	Std	1	Std	1	Std	
2.136	2.513	2.416	2.842	2.402	2.825	2.423	2.85	2.409	2.833	ns

Table 170 LVDS25 Transmitter Characteristics for MSIO I/O Bank (Output and Tristate Buffers)

	T _{DP}		T _{ZL}		T _{ZH}		T _{HZ}		T _{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
No pre-emphasis	1.61	1.893	1.749	2.051	1.735	2.041	1.897	2.231	1.866	2.195	ns
Min pre-emphasis	1.527	1.796	1.757	2.067	1.744	2.052	1.905	2.241	1.876	2.207	ns
Med pre-emphasis	1.496	1.76	1.765	2.027	1.751	2.06	1.914	2.252	1.884	2.216	ns

LVDS33 AC Switching Characteristics

Table 171 LVDS33 Receiver Characteristics for MSIO I/O Bank (Input Buffers)

On Die Termination (ODT)	T _{py}		
	1	Std	Unit
None	2.572	3.025	ns
100	2.569	3.023	ns

Table 172 LVDS33 Transmitter Characteristics for MSIO I/O Bank (Output and Tristate Buffers)

T _{DP}		T _{ZL}		T _{ZH}		T _{HZ}		T _{LZ}		Unit
1	Std	1	Std	1	Std	1	Std	1	Std	
1.942	2.284	1.98	2.33	1.97	3.28	1.953	2.298	1.96	2.307	ns

AC Switching Characteristics

Worst commercial-case conditions: $T = 85\text{ }^{\circ}\text{C}$, $V_D = 1.14\text{ V}$, $V_{DI} = 2.375\text{ V}$.

Table 210 RSDS AC Switching Characteristics for Receiver (for MSIO I/O Bank - Input Buffers)

On-Die Termination (ODT)	T_{PY}		Unit
	1	Std	
None	2.855	3.359	ns
100	2.85	3.353	ns

Table 211 RSDS AC Switching Characteristics for Receiver (for MSIOD I/O Bank - Input Buffers)

On-Die Termination (ODT)	T_{PY}		Unit
	1	Std	
None	2.602	3.061	ns
100	2.597	3.055	ns

Table 212 RSDS AC Switching Characteristics for Transmitter (for MSIO I/O Bank - Output and Tristate Buffers)

T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
1	Std	1	Std	1	Std	1	Std	1	Std	
2.097	2.467	2.303	2.709	2.291	1.925	1.961	2.307	1.947	2.29	ns

Table 213 RSDS AC Switching Characteristics for Transmitter (for MSIOD I/O Bank Output and Tristate Buffers)

	T_{DP}		T_{ZL}		T_{ZH}		T_{HZ}		T_{LZ}		Unit
	1	Std	1	Std	1	Std	1	Std	1	Std	
No pre-emphasis	1.614	1.899	1.559	1.834	1.55	1.823	1.59	1.87	1.575	1.852	ns
Min pre-emphasis	1.604	1.887	1.742	2.051	1.728	2.032	1.889	2.222	1.858	2.185	ns
Med pre-emphasis	1.521	1.79	1.753	2.02	1.737	2.043	1.9	2.235	1.868	2.197	ns
Max pre-emphasis	1.492	1.754	1.762	2.073	1.745	2.052	1.91	2.247	1.876	2.206	ns

2.3.7.6 LVPECL

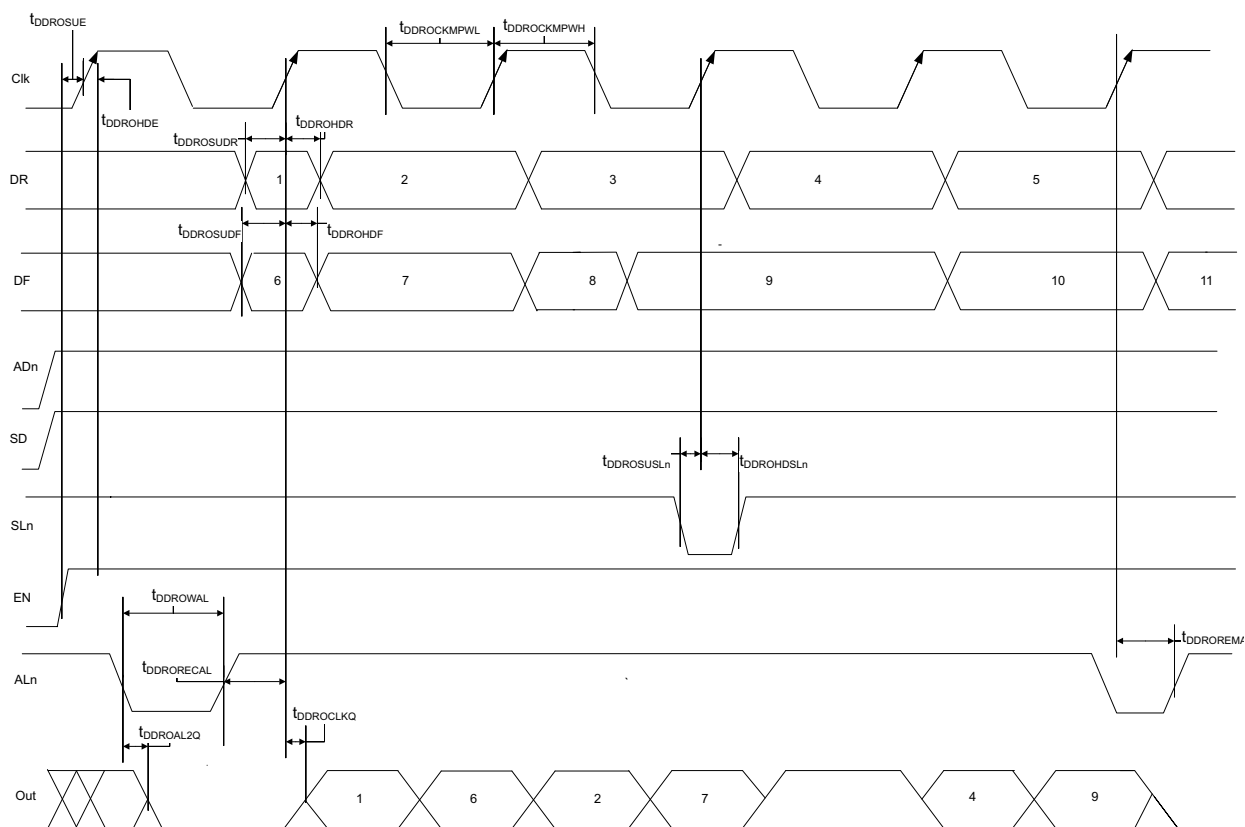
Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Similar to LVDS, two pins are needed. It also requires external resistor termination. IGLOO2 and SmartFusion2 SoC FPGAs support only LVPECL receivers and do not support LVPECL transmitters.

Minimum and Maximum Input and Output Levels (Applicable to MSIO I/O Bank Only)

Table 214 LVPECL Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{DI}	3.15	3.3	3.45	V

Figure 13 Output DDR Timing Diagram



2.3.9.5 Timing Characteristics

The following table lists the output DDR propagation delays in worst commercial-case conditions when $T_J = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 222 Output DDR Propagation Delays

Symbol	Description	Measuring Nodes (from, to)	1	Std	Unit
$T_{DDROCLKQ}$	Clock-to-out of DDR for output DDR	E, G	0.263	0.309	ns
$T_{DDROSUDF}$	Data_F data setup for output DDR	F, E	0.143	0.168	ns
$T_{DDROSUDR}$	Data_R data setup for output DDR	A, E	0.19	0.223	ns
$T_{DDROHDF}$	Data_F data hold for output DDR	F, E	0	0	ns
$T_{DDROHDR}$	Data_R data hold for output DDR	A, E	0	0	ns
$T_{DDROSUE}$	Enable setup for input DDR	B, E	0.419	0.493	ns
T_{DDROHE}	Enable hold for input DDR	B, E	0	0	ns
$T_{DDROSUSLn}$	Synchronous load setup for input DDR	D, E	0.196	0.231	ns
$T_{DDROHSLn}$	Synchronous load hold for input DDR	D, E	0	0	ns
$T_{DDROAL2Q}$	Asynchronous load-to-out for output DDR	C, G	0.528	0.621	ns
$T_{DDROREMA}$	Asynchronous load removal time for output DDR	C, E	0	0	ns
$T_{DDRORECAL}$	Asynchronous load recovery time for output DDR	C, E	0.034	0.04	ns

2.3.11 Global Resource Characteristics

The IGLOO2 and SmartFusion2 SoC FPGA devices offer a powerful, low skew global routing network which provides an effective clock distribution throughout the FPGA fabric. See 445: IGLOO2 FPGA and SmartFusion2 SoC FPGA Fabric User Guide for the positions of various global routing resources.

The following table lists the 150 device global resources in worst commercial-case conditions when $T_J = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 225 150 Device Global Resource

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	R_{CKL}^T	0.83	0.911	0.831	0.913	ns
Input high delay for global clock	R_{CKH}^T	1.457	1.588	1.715	1.869	ns
Maximum skew for global clock	R_{CKSW}^T		0.131		0.154	ns

The following table lists the 090 device global resources in worst commercial-case conditions when $T_J = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 226 090 Device Global Resource

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	R_{CKL}^T	0.835	0.888	0.833	0.886	ns
Input high delay for global clock	R_{CKH}^T	1.405	1.489	1.654	1.752	ns
Maximum skew for global clock	R_{CKSW}^T		0.084		0.098	ns

The following table lists the 050 device global resources in worst commercial-case conditions when $T_J = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 227 050 Device Global Resource

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	R_{CKL}^T	0.827	0.897	0.826	0.896	ns
Input high delay for global clock	R_{CKH}^T	1.419	1.53	1.671	1.8	ns
Maximum skew for global clock	R_{CKSW}^T		0.111		0.129	ns

The following table lists the 025 device global resources in worst commercial-case conditions when $T_J = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 228 025 Device Global Resource

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	R_{CKL}^T	0.747	0.799	0.745	0.797	ns
Input high delay for global clock	R_{CKH}^T	1.294	1.378	1.522	1.621	ns
Maximum skew for global clock	R_{CKSW}^T		0.084		0.099	ns

Table 232 RAM1K18 Dual-Port Mode for Depth \times Width Configuration 2K \times 4 (continued)

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Address setup time	\overline{A} DRSU	0.475		0.559		ns
Address hold time	\overline{A} DRHD	0.274		0.322		ns
Data setup time	\overline{D} SU	0.336		0.395		ns
Data hold time	\overline{D} HD	0.082		0.096		ns
Block select setup time	\overline{B} LKSU	0.207		0.244		ns
Block select hold time	\overline{B} LKHHD	0.216		0.254		ns
Block select to out disable time (when pipelined register disabled)	\overline{B} LK2Q		1.529		1.799	ns
Block select minimum pulse width	\overline{B} LKMPW	0.186		0.219		ns
Read enable setup time	\overline{R} DESU	0.485		0.57		ns
Read enable hold time	\overline{R} DEHD	0.071		0.083		ns
Pipelined read enable setup time (A_DOUT_EN, B_DOUT_EN)	\overline{T} RDPLESU	0.248		0.291		ns
Pipelined read enable hold time (A_DOUT_EN, B_DOUT_EN)	\overline{T} RDPLEHD	0.102		0.12		ns
Asynchronous reset to output propagation delay	\overline{R} 2Q \overline{T}		1.514		1.781	ns
Asynchronous reset removal time	\overline{R} STREM	0.506		0.595		ns
Asynchronous reset recovery time	\overline{R} STREC	0.004		0.005		ns
Asynchronous reset minimum pulse width	\overline{R} STMPW	0.301		0.354		ns
Pipelined register asynchronous reset removal time	\overline{P} L \overline{R} STREM	0.279		0.328		ns
Pipelined register asynchronous reset recovery time	\overline{P} L \overline{R} STREC	0.327		0.385		ns
Pipelined register asynchronous reset minimum pulse width	\overline{P} L \overline{R} STMPW	0.282		0.332		ns
Synchronous reset setup time	\overline{S} RSTSU	0.226		0.265		ns
Synchronous reset hold time	\overline{S} RSTHD	0.036		0.043		ns
Write enable setup time	\overline{W} ESU	0.415		0.488		ns
Write enable hold time	\overline{W} EHD	0.048		0.057		ns
Maximum frequency	\overline{F} MAX		400		340	MHz

The following table lists the RAM1K18 dual-port mode for depth \times width configuration 4K \times 4 in worst commercial-case conditions when $T = 85^\circ\text{C}$, $V_D = 1.14\text{ V}$.

 Table 233 RAM1K18 Dual-Port Mode for Depth \times Width Configuration 4K \times 4

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Clock period	\overline{T} CY	2.5		2.941		ns
Clock minimum pulse width high	\overline{C} LKMPWH	1.125		1.323		ns
Clock minimum pulse width low	\overline{C} LKMPWL	1.125		1.323		ns
Pipelined clock period	\overline{P} LCY	2.5		2.941		ns
Pipelined clock minimum pulse width high	\overline{P} LCLKMPWH	1.125		1.323		ns

The following table lists the RAM1K18 dual-port mode for depth \times width configuration 8K \times 2 in worst commercial-case conditions when $T = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 234 RAM1K18 Dual-Port Mode for Depth \times Width Configuration 8K \times 2

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Clock period	T_{CY}	2.5		2.941		ns
Clock minimum pulse width high	$CLKMPWH$	1.125		1.323		ns
Clock minimum pulse width low	$CLKMPWL$	1.125		1.323		ns
Pipelined clock period	$PLCY$	2.5		2.941		ns
Pipelined clock minimum pulse width high	$PLCLKMPWH$	1.125		1.323		ns
Pipelined clock minimum pulse width low	$PLCLKMPWL$	1.125		1.323		ns
Read access time with pipeline register			0.32		0.377	ns
Read access time without pipeline register	T_{CLK2Q}			2.272		ns
Access time with feed-through write timing				1.511		ns
Address setup time	A_{DDRSU}	0.612		0.72		ns
Address hold time	A_{DDRHD}	0.274		0.322		ns
Data setup time	D_{SU}	0.33		0.388		ns
Data hold time	D_{HD}	0.082		0.096		ns
Block select setup time	$BLKSU$	0.207		0.244		ns
Block select hold time	$BLKHD$	0.216		0.254		ns
Block select to out disable time (when pipelined register disabled)	T_{BLK2Q}		1.511		1.778	ns
Block select minimum pulse width	$BLKMPW$	0.186		0.219		ns
Read enable setup time	R_{DESU}	0.529		0.622		ns
Read enable hold time	R_{DEHD}	0.071		0.083		ns
Pipelined read enable setup time (A_DOUT_EN, B_DOUT_EN)	$T_{RDPLESU}$	0.248		0.291		ns
Pipelined read enable hold time (A_DOUT_EN, B_DOUT_EN)	$T_{RDPLEHD}$	0.102		0.12		ns
Asynchronous reset to output propagation delay	$R_{2Q} T$		1.528		1.797	ns
Asynchronous reset removal time	R_{STREM}	0.506		0.595		ns
Asynchronous reset recovery time	R_{STREC}	0.004		0.005		ns
Asynchronous reset minimum pulse width	R_{STMPW}	0.301		0.354		ns
Pipelined register asynchronous reset removal time	PLR_{STREM}	0.279		0.328		ns
Pipelined register asynchronous reset recovery time	PLR_{STREC}	0.327		0.385		ns
Pipelined register asynchronous reset minimum pulse width	PLR_{STMPW}	0.282		0.332		ns
Synchronous reset setup time	S_{RSTSU}	0.226		0.265		ns
Synchronous reset hold time	S_{RSTHD}	0.036		0.043		ns
Write enable setup time	W_{ESU}	0.488		0.574		ns
Write enable hold time	W_{EHD}	0.048		0.057		ns
Maximum frequency	f_{MAX}		400		340	MHz

The following table lists the RAM1K18 two-port mode depth \times width configuration 512 \times 36 in worst commercial-case conditions when $T = 85\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 236 RAM1K18 Two-Port Mode for Depth \times Width Configuration 512 \times 36

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Clock period	T_{CY}	2.5		2.941		ns
Clock minimum pulse width high	$CLKMPWH$	1.125		1.323		ns
Clock minimum pulse width low	$CLKMPWL$	1.125		1.323		ns
Pipelined clock period	T_{PLCY}	2.5		2.941		ns
Pipelined clock minimum pulse width high	$PLCLKMPWH$	1.125		1.323		ns
Pipelined clock minimum pulse width low	$PLCLKMPWL$	1.125		1.323		ns
Read access time with pipeline register	T_{CLK2Q}		0.334		0.393	ns
Read access time without pipeline register				2.25		2.647
Address setup time	A_{DDRSU}	0.313		0.368		ns
Address hold time	A_{DDRHD}	0.274		0.322		ns
Data setup time	D_{SU}	0.337		0.396		ns
Data hold time	D_{HD}	0.111		0.13		ns
Block select setup time	BLK_{SU}	0.207		0.244		ns
Block select hold time	BLK_{HD}	0.201		0.237		ns
Block select to out disable time (when pipelined register is disabled)	T_{BLK2Q}		2.25		2.647	ns
Block select minimum pulse width	BLK_{MPW}	0.186		0.219		ns
Read enable setup time	R_{DESU}	0.449		0.528		ns
Read enable hold time	R_{DEHD}	0.167		0.197		ns
Pipelined read enable setup time (A_DOUT_EN, B_DOUT_EN)	R_{DPLESU}	0.248		0.291		ns
Pipelined read enable hold time (A_DOUT_EN, B_DOUT_EN)	R_{DPLEHD}	0.102		0.12		ns
Asynchronous reset to output propagation delay	$R2Q\ T$		1.506		1.772	ns
Asynchronous reset removal time	R_{STREM}	0.506		0.595		ns
Asynchronous reset recovery time	R_{STREC}	0.004		0.005		ns
Asynchronous reset minimum pulse width	R_{STMPW}	0.301		0.354		ns
Pipelined register asynchronous reset removal time	PLR_{STREM}	0.279		0.328		ns
Pipelined register asynchronous reset recovery time	PLR_{STREC}	0.327		0.385		ns
Pipelined register asynchronous reset minimum pulse width	PLR_{STMPW}	0.282		0.332		ns
Synchronous reset setup time	S_{RSTSU}	0.226		0.265		ns
Synchronous reset hold time	S_{RSTHD}	0.036		0.043		ns
Write enable setup time	W_{ESU}	0.39		0.458		ns
Write enable hold time	W_{EHD}	0.242		0.285		ns
Maximum frequency	F_{MAX}		400		340	MHz

Table 239 μ SRAM (RAM128x9) in 128 x 9 Mode (continued)

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Read asynchronous reset removal time (pipelined clock)		0.023		0.027		ns
Read asynchronous reset removal time (non-pipelined clock)	T_{RSTREM}	0.046		0.054		ns
Read asynchronous reset recovery time (pipelined clock)		0.507		0.597		ns
Read asynchronous reset recovery time (non-pipelined clock)	T_{RSTREC}	0.236		0.278		ns
Read asynchronous reset to output propagation delay (with pipelined register enabled)	T_{R2O}		0.835		0.982	ns
Read synchronous reset setup time	T_{SRSTSU}	0.271		0.319		ns
Read synchronous reset hold time	T_{SRSTHD}	0.061		0.071		ns
Write clock period	T_{CY}	4		4		ns
Write clock minimum pulse width high	$T_{CCLKMPWH}$	1.8		1.8		ns
Write clock minimum pulse width low	$T_{CCLKMPWL}$	1.8		1.8		ns
Write block setup time	T_{BLKCSU}	0.404		0.476		ns
Write block hold time	T_{BLKCHD}	0.007		0.008		ns
Write input data setup time	T_{DINCSU}	0.115		0.135		ns
Write input data hold time	T_{DINCHD}	0.15		0.177		ns
Write address setup time	$T_{ADDRCSU}$	0.088		0.104		ns
Write address hold time	$T_{ADDRCHD}$	0.128		0.15		ns
Write enable setup time	$T_{WEC SU}$	0.397		0.467		ns
Write enable hold time	T_{WECHD}	0.026		0.03		ns
Maximum frequency	F_{MAX}		250		250	MHz

The following table lists the μ SRAM in 128 x 8 mode in worst commercial-case conditions when $T_J = 85^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 240 μ SRAM (RAM128x8) in 128 x 8 Mode

Parameter	Symbol	1		Std		Unit
		Min	Max	Min	Max	
Read clock period	T_{CY}	4		4		ns
Read clock minimum pulse width high	$T_{CLKMPWH}$	1.8		1.8		ns
Read clock minimum pulse width low	$T_{CLKMPWL}$	1.8		1.8		ns
Read pipeline clock period	T_{PCY}	4		4		ns
Read pipeline clock minimum pulse width high	$T_{PLCLKMPWH}$	1.8		1.8		ns
Read pipeline clock minimum pulse width low	$T_{PLCLKMPWL}$	1.8		1.8		ns
Read access time with pipeline register			0.266		0.313	ns
Read access time without pipeline register	T_{CLK2O}			1.677		ns
Read address setup time in synchronous mode		0.301		0.354		ns
Read address setup time in asynchronous mode	T_{ADDRSU}		1.856		2.184	ns

Table 265 Programming Times with 100 kHz, 25 MHz and 12.5 MHz SPI Clock Rates (Fabric Only)

M2S/M2GL Device	Auto Programming			Auto Update	Programming Recovery		Unit
	100 kHz	25 MHz	12.5 MHz	25 MHz	12.5 MHz		
005	69	49	50				Sec
010	99	57	57				Sec
025	150	64	63				Sec
050	55	Not Supported		Not Supported			Sec
060	313	105	104				Sec
090	449	131	130				Sec
150	730	179	183				Sec

1. Auto programming in 050 device is done through SC_SPI, and SPI CLK is set to 6.25 MHz.

Table 266 Programming Times with 100 kHz, 25 MHz and 12.5 MHz SPI Clock Rates (eNVM Only)

M2S/M2GL Device	Auto Programming			Auto Update	Programming Recovery		Unit
	100 kHz	25 MHz	12.5 MHz	25 MHz	12.5 MHz		
005	63	70	71				Sec
010	108	109	109				Sec
025	109	107	108				Sec
050	107	Not Supported		Not Supported			Sec
060	100	108	108				Sec
090	176	184	184				Sec
150	183	183	183				Sec

Table 267 Programming Times with 100 kHz, 25 MHz and 12.5 MHz SPI Clock Rates (Fabric and eNVM)

M2S/M2GL Device	Auto Programming			Auto Update	Programming Recovery		Unit
	100 kHz	25 MHz	12.5 MHz	25 MHz	12.5 MHz		
005	109	89	88				Sec
010	183	135	135				Sec
025	251	142	143				Sec
050	134	Not Supported		Not Supported			Sec
060	390	183	180				Sec
090	604	283	282				Sec
150	889	331	332				Sec

2.3.22 JTAG

Table 284 JTAG 1532 for 005, 010, 025, and 050 Devices

Parameter	Symbol	005		010		025		050		Unit
		1	Std	1	Std	1	Std	1	Std	
Clock to Q (data out)	T_{TCK2Q}	7.47	8.79	7.73	9.09	7.75	9.12	7.89	9.28	ns
Reset to Q (data out)	T_{RSTB2Q}	7.65	9	6.43	7.56	6.13	7.21	7.40	8.70	ns
Test data input setup time	T_{DISU}	1.05	0.89	0.69	0.59	0.67	0.57	0.30	0.25	ns
Test data input hold time	T_{DIHD}	2.38	2.8	2.38	2.8	2.42	2.85	2.09	2.45	ns
Test mode select setup time	T_{TMSSU}	0.73	0.62	1.03	1.21	1.1	0.94	0.28	0.33	ns
Test mode select hold time	T_{TMDHD}	1.36	1.6	1.43	1.68	1.93	2.27	0.16	0.19	ns
ResetB removal time	$T_{TRSTREM}$	0.77	0.65	1.08	0.92	1.33	1.13	0.45	0.38	ns
ResetB recovery time	$T_{TRSTREC}$	0.76	0.65	1.07	0.91	1.34	1.14	0.45	0.38	ns
TCK maximum frequency	F_{TCKMAX}	25	21.25	25	21.25	25	21.25	25.00	21.25	MHz

Table 285 JTAG 1532 for 060, 090, and 150 Devices

Parameter	Symbol	060		090		150		Unit
		1	Std	1	Std	1	Std	
Clock to Q (data out)	T_{TCK2Q}	8.38	9.86	8.96	10.54	8.66	10.19	ns
Reset to Q (data out)	T_{RSTB2Q}	8.54	10.04	7.75	9.12	8.79	10.34	ns
Test data input setup time	T_{DISU}	1.18	1	1.31	1.11	0.96	0.82	ns
Test data input hold time	T_{DIHD}	2.52	2.97	2.68	3.15	2.57	3.02	ns
Test mode select setup time	T_{TMSSU}	0.97	0.83	1.02	0.87	0.53	0.45	ns
Test mode select hold time	T_{TMDHD}	1.7	2	1.67	1.96	1.02	1.2	ns
ResetB removal time	$T_{TRSTREM}$	1.21	1.03	0.76	0.65	1.03	0.88	ns
ResetB recovery time	$T_{TRSTREC}$	1.21	1.03	0.77	0.65	1.03	0.88	ns
TCK maximum frequency	F_{TCKMAX}	25	21.25	25	21.25	25	21.25	MHz

2.3.23 System Controller SPI Characteristics

The following table lists the IGLOO2 DEVRST_N to functional times in worst-case industrial conditions when $T_j = 100\text{ }^\circ\text{C}$, $V_D = 1.14\text{ V}$.

Table 292 DEVRST_N to Functional Times for IGLOO2

Symbol	From	To	Description	Maximum Power-up to Functional Time for IGLOO2 (uS)						
				005	010	025	050	060	090	150
$T_{POR2OUT}$	POWER_ON_RESET_N	Output available at I/O	Fabric to output	114	116	113	113	115	115	114
$T_{DEVRST2OUT}$	DEVRST_N	Output available at I/O	V_{DD} at its minimum threshold level to output	314	353	314	307	343	341	341
$T_{DEVRST2POR}$	DEVRST_N	POWER_ON_RESET_N	V_{DD} at its minimum threshold level to fabric	200	238	201	195	230	229	227
$T_{DEVRST2WPU}$	DEVRST_N	DDRIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIOD Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215